

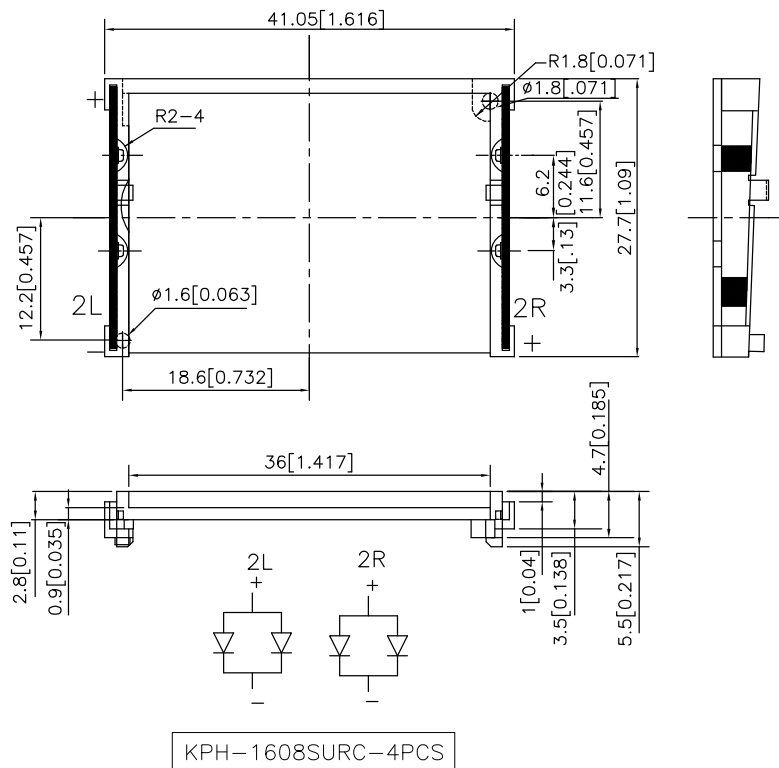
Features

- LOW POWER REQUIREMENTS.
- LARGE AREA, UNIFORM, BRIGHT LIGHT EMITTING SURFACE.
- EASY FOR INSTALLATION.
- LOW POWER CONSUMPTION.
- RoHS COMPLIANT.

Description

The Hyper Red source color devices are made with DH InGaAlP on GaAs substrate Light Emitting Diode.

Package Dimensions & Internal Circuit Diagram



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.
4. Specifications are subject to change without notice.

Selection Guide

Part No.	Dice	Lens Type	Ev (lux) @ 80mA	
			Min.	Typ.
GLP-003/1608SURC	HYPER RED (InGaAlP)	WATER CLEAR	69	103

Note:

1. Test circuit: The chips are four in parallel.

Electrical / Optical Characteristics at T_A=25°C

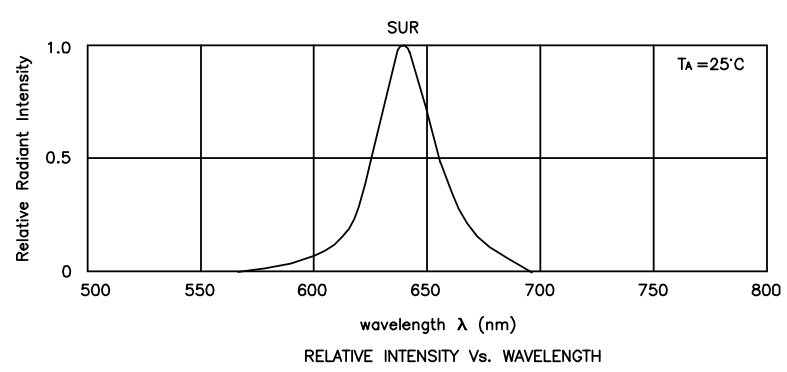
Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
λ_{peak}	Peak Wavelength	Hyper Red	640		nm	I _F =20mA
λ_D	Dominant Wavelength	Hyper Red	628		nm	I _F =20mA
$\Delta\lambda_{1/2}$	Spectral Line Half-width	Hyper Red	27		nm	I _F =20mA
C	Capacitance	Hyper Red	45		pF	V _F =0V; f=1MHz
V _F	Forward Voltage (Per chip)	Hyper Red	1.9	2.5	V	I _F =20mA
I _R	Reverse Current (Per chip)	Hyper Red		10	uA	V _R = 5V

Absolute Maximum Ratings at T_A=25°C

Parameter	Hyper Red	Units
Power dissipation (Per chip)	170	mW
Forward Current (Per chip)	30	mA
Peak Forward Current [1] (Per chip)	185	mA
Reverse Voltage (Per chip)	5	V
Operating / Storage Temperature	-40°C To +85°C	

Note:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.



Hyper Red GLP-003/1608SURC

